

A1298





## ■MAXIMUM RATINGS (Ta=25℃) 最大額定値

Characteristic 特性參數	SymbolRating符號額定值		Unit 單位	
Collector-Base Voltage 集電極-基極電壓	V <sub>CBO</sub>	-35	V	
Collector-Emitter Voltage 集電極-發射極電壓	V <sub>CEO</sub>	-30	V	
Emitter-Base Voltage 發射極-基極電壓	$\mathrm{V}_{\mathrm{EBO}}$	-5	V	
Collector Current-Continuous 集電極電流-連續	Ic	-800	mA	
Collector Power Dissipation 集電極耗散功率	P <sub>C</sub>	225	mW	
Junction Temperature 結溫	T <sub>i</sub>	150	°C	
Storage Temperature Range 儲存溫度	T <sub>stg</sub>	-55~150	°C	

## ■DEVICE MARKING 打標

A1298	0	Y	
MARK	ΙO	ΙY	
$H_{FE1}$	100~200	160~320	



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## ■ELECTRICAL CHARACTERISTICS 電特性

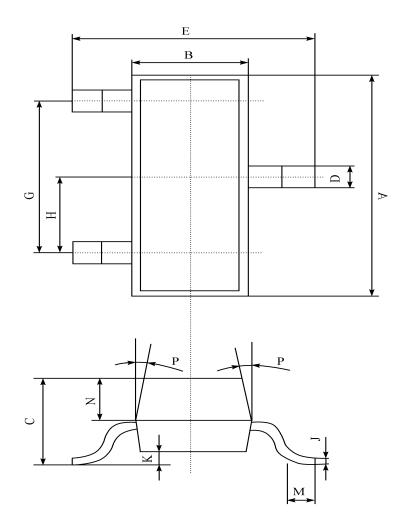
(T<sub>A</sub>=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

Characteristic 特性參數	Symbol 符號	Test Condition 測試條件	Min 最小値	Typ 典型値	Max 最大値	Unit 單位
Collector Cutoff Current 集電極截止電流	I <sub>CBO</sub>	$V_{CB}=-35V,$ $I_{E}=0$			-0.1	μA
Emitter Cutoff Current 發射極截止電流	I <sub>ebo</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100 μ A	-35			V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1.0mA	-30		_	V
Emitter-Base Breakdown Votlage 發射極-基極擊穿電壓	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100 μ A	-5			V
DC Current Gain 直流電流增益	$\mathrm{H}_{\mathrm{FE1}}$	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	100		320	
DC Current Gain 直流電流增益	H <sub>FE2</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA	40			
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-20mA			-0.4	V
Base-Emitter Saturation 基極-發射極電壓	$V_{BE}$	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	-0.5		-0.8	V
Transition Frequency 特徵頻率	$\mathbf{f}_{\mathrm{T}}$	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA		120		MHz
Collector Output Capacitance 輸出電容	C <sub>ob</sub>	$V_{CB}$ =-10V, $I_{E}$ =0, f=1MHz		13	_	pF



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## ■DIMENSION 外形封裝尺寸



序號	數值及公差
А	$2.90 \pm 0.10$
В	$1.30 \pm 0.10$
С	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
Е	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
Н	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	0.00-0.10
М	≥0.2
N	$0.60 \pm 0.10$
Р	$7\pm2°$

This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <a href="http://www.takcheong.com">http://www.takcheong.com</a>.

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